

SKiiP® 3

2-pack-integrated intelligent Power System

Power Section

SKiiP 1513GB122-3DL

Data

Power section features

- SKiiP technology inside
- SPT (Soft Punch Trough) IGBTs
- CAL diode technology
- Integrated current sensor
- Integrated temperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP® 3 System)
- IEC 60068-1 (climate) 40/125/56
- UL recognized File no. E63532

1) with assembly of suitable MKP capacitor per terminal

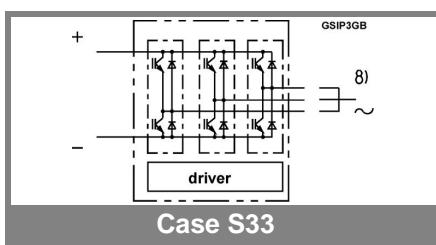
8) AC connection busbars must be connected by the user; copper busbars available on request

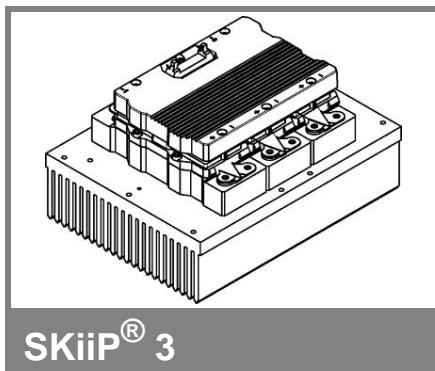
Absolute Maximum Ratings		$T_s = 25^\circ\text{C}$ unless otherwise specified		
Symbol	Conditions	Values		Units
IGBT				
V_{CES}		1200		V
$V_{CC}^{1)}$	Operating DC link voltage	900		V
V_{GES}		± 20		V
I_C	$T_s = 25 \text{ (70)}^\circ\text{C}$	1500 (1125)		A
Inverse diode				
$I_F = -I_C$	$T_s = 25 \text{ (70)}^\circ\text{C}$	1340 (1020)		A
I_{FSM}	$T_j = 150^\circ\text{C}$, $t_p = 10 \text{ ms}$; sin	10200		A
I^2t (Diode)	Diode, $T_j = 150^\circ\text{C}$, 10 ms	520		kA²s
$T_{j1} (T_{stg})$		- 40 ... + 150 (125)		°C
V_{isol}	rms, AC, 1 min, main terminals to heat sink	3000		V
$I_{AC\text{-terminal}}$	per AC terminal, rms, $T_s = 70^\circ\text{C}$,	400		A
	$T_{\text{terminal}} < 115^\circ\text{C}$			

Characteristics		$T_s = 25^\circ\text{C}$ unless otherwise specified		
Symbol	Conditions	min.	typ.	max.
IGBT				
V_{CEsat}	$I_C = 900 \text{ A}$, $T_j = 25 \text{ (125)}^\circ\text{C}$; measured at terminal	2,3 (2,5)	2,6	V
V_{CEO}	$T_j = 25 \text{ (125)}^\circ\text{C}$; at terminal	1,1 (1)	1,3 (1,2)	V
r_{CE}	$T_j = 25 \text{ (125)}^\circ\text{C}$; at terminal	1,3 (1,7)	1,5 (1,9)	mΩ
I_{CES}	$V_{GE} = 0 \text{ V}$, $V_{CE} = V_{CES}$, $T_j = 25 \text{ (125)}^\circ\text{C}$	3,6 (108)		mA
$E_{on} + E_{off}$	$I_C = 900 \text{ A}$, $V_{CC} = 600 \text{ V}$ $T_j = 125^\circ\text{C}$, $V_{CC} = 900 \text{ V}$	270		mJ
$R_{CC+EE'}$	terminal chip, $T_j = 25^\circ\text{C}$	0,17		mΩ
L_{CE}	top, bottom	4		nH
C_{CHC}	per phase, AC-side	5,1		nF
Inverse diode				
$V_F = V_{EC}$	$I_F = 900 \text{ A}$, $T_j = 25 \text{ (125)}^\circ\text{C}$ measured at terminal	1,95 (1,7)	2,1	V
V_{TO}	$T_j = 25 \text{ (125)}^\circ\text{C}$	1,1 (0,8)	1,2 (0,9)	V
r_T	$T_j = 25 \text{ (125)}^\circ\text{C}$	0,9 (1)	1 (1,2)	mΩ
E_{rr}	$I_C = 900 \text{ A}$, $V_{CC} = 600 \text{ V}$ $T_j = 125^\circ\text{C}$, $V_{CC} = 900 \text{ V}$	72		mJ
		92		mJ
Mechanical data				
M_{dc}	DC terminals, SI Units	6	8	Nm
M_{ac}	AC terminals, SI Units	13	15	Nm
w	SKiiP® 3 System w/o heat sink		2,4	kg
w	heat sink		7,5	kg

Thermal characteristics (PX 16 heat sink with fan SKF 16B-230-1); "s" reference to heat sink; "r" reference to built-in temperature sensor (acc. IEC 60747-15)				
$R_{th(j-s)I}$	per IGBT			0,02
$R_{th(j-s)D}$	per diode			0,038
Z_{th}	R_i (mK/W) (max. values)		tau_i(s)	
1	2	3	4	1 2 3 4
3,4	9,6	7	0	363 0,18 0,04 1
12	12	18	20	30 5 0,25 0,04
2,1	20	5,5	1,4	210 85 11 0,4

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2-pack-integrated intelligent Power System

**2-pack
integrated gate driver
SKiiP 1513GB122-3DL**

Data

Gate driver features

- CMOS compatible inputs
- Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature and DC-bus voltage (option)
- Short circuit protection
- Over current protection
- Over voltage protection (option)
- Power supply protection against under voltage
- Interlock of top/bottom switch
- Isolation by transformers
- Fibre optic interface (option for GB-types only)
- IEC 60068-1 (climate) 40/85/56
- UL recognized file no. 242581

Absolute Maximum Ratings		$T_a = 25 \text{ }^{\circ}\text{C}$ unless otherwise specified	
Symbol	Conditions	Values	Units
V_{S2}	unstabilized 24 V power supply	30	V
V_i	input signal voltage (high)	15 + 0,3	V
dv/dt	secondary to primary side	75	kV/ μ s
V_{isolIO}	input / output (AC, rms, 2)	3000	V
V_{isolPD}	partial discharge extinction voltage, rms, $Q_{PD} \leq 10 \text{ pC}$	1170	V
V_{isol12}	output 1 / output 2 (AC, rms, 2 s)	1500	V
f_{sw}	switching frequency	10	kHz
f_{out}	output frequency for $I_{peak(1)} = I_C$	10	kHz
$T_{op} (T_{stg})$	operating / storage temperature	- 40 ... + 85	$^{\circ}\text{C}$

Characteristics ($T_a = 25 \text{ }^{\circ}\text{C}$)						
Symbol	Conditions	min.	typ.	max.		
V_{S2}	supply voltage non stabilized	13	24	30		
I_{S2}	$V_{S2} = 24 \text{ V}$	$278+29*f/\text{kHz}+0,00015*(I_{AC}/A)^2$				
V_{IT+}	input threshold voltage (High)	12,3				
V_{IT-}	input threshold voltage (Low)	4,6				
R_{IN}	input resistance	10				
C_{IN}	input capacitance	1				
$t_{d(on)IO}$	input-output turn-on propagation time	1,3				
$t_{d(off)IO}$	input-output turn-off propagation time	1,3				
$t_{pERRRESET}$	error memory reset time	9				
t_{TD}	top / bottom switch interlock time	3,3				
$I_{analogOUT}$	max. 5mA; 8 V corresponds to 15 V supply voltage for external components	1500				
I_{s1out}	max. load current	50				
I_{TRIPSC}	over current trip level ($I_{analog OUT} = 10 \text{ V}$)	1875				
T_{tp}	over temperature protection	110	120			
U_{DCTRIP}	$U_{DC\text{-protection}} (U_{analog OUT} = 9 \text{ V})$; (option for GB types)	not implemented				

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